

# ESRF X-ray Detector Workshop

Feb 13-14, 2003

(held in conjunction with the ESRF Annual Users' Meeting)

## A Synopsis

Graham Smith

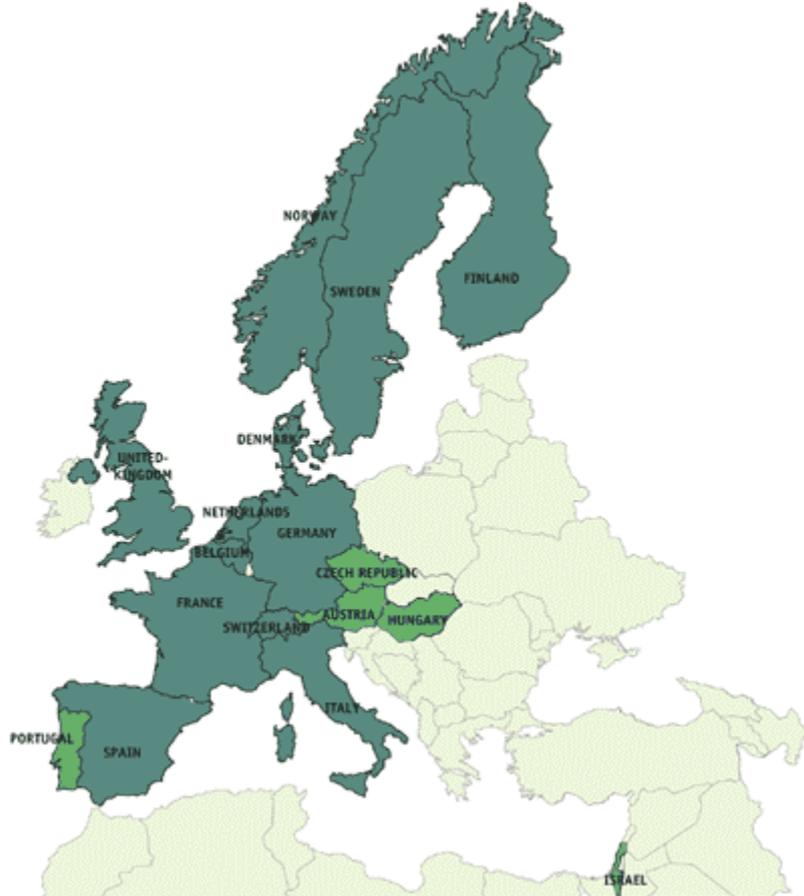
Instrumentation Division

(IO Seminar Series, February 26, 2003)

# ESRF (European Synchrotron Radiation Facility) in Grenoble



# ESRF Annual Budget ~ \$60M



## Members' share in contribution to the annual budget:

27.5%	France
25.5%	Germany
15%	Italy
14%	United Kingdom
4%	Spain
4%	Switzerland
6%	Benesync (Belgium, Netherlands)
4%	Nordsync (Denmark, Finland, Norway, Sweden)

## Additional contributions

(percentages refer to Members' total contribution):

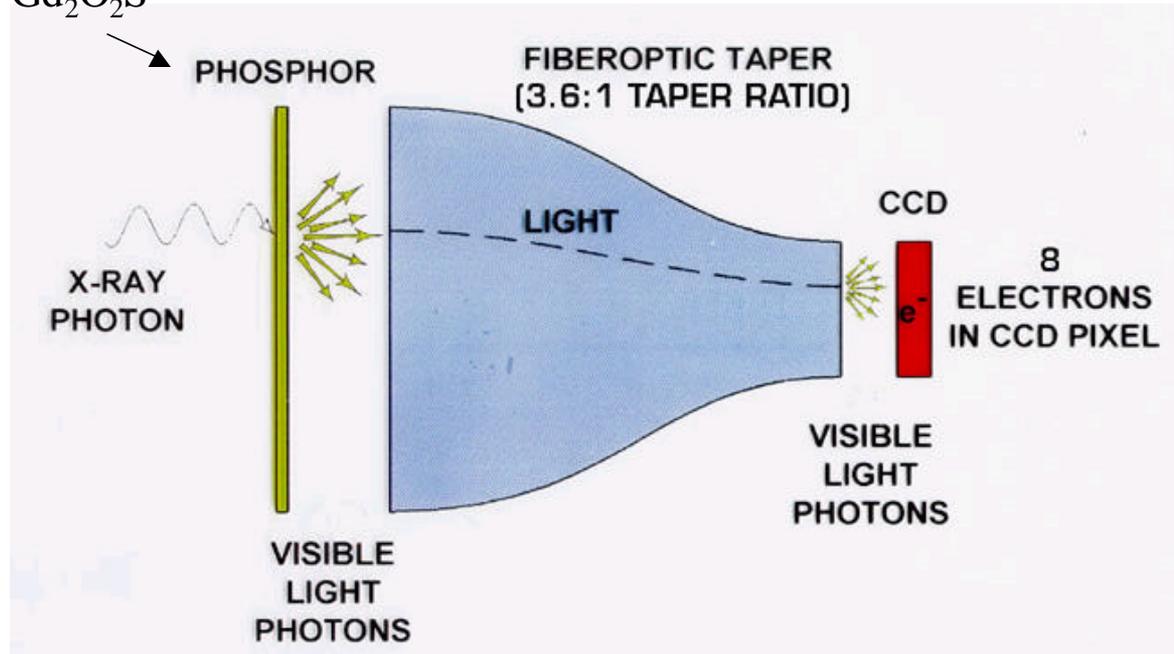
1%	Portugal
1%	Israel
1%	Austria
0.38%	Czech Republic
0.2%	Hungary

Workshop Program: <http://www.esrf.fr/>

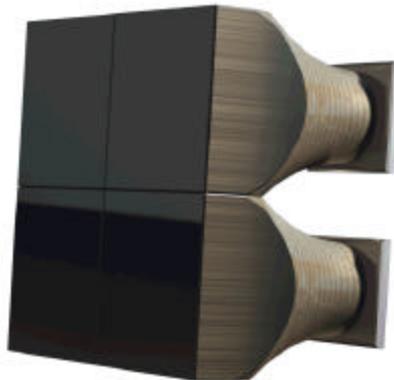
Imaging	Phosphor/CCD	Ron Hamlin, ADSC Sol Gruner, CHESS
	Solid State Pixels	Michael Campbell, CERN Sol Gruner, CHESS Jules Hendrix, MAR Research
	WAXS	MSGCs at ESRF
Spectroscopy	Energy Dispersive EXAFS	Jon Headspith, Rutherford Laboratory, UK
	Compound Semiconductors	Alan Owens, ESA/ESTEC, The Netherlands
	Cryogenic detectors	Stephan Friedrich, LLNL

# Phosphor coupled to CCD

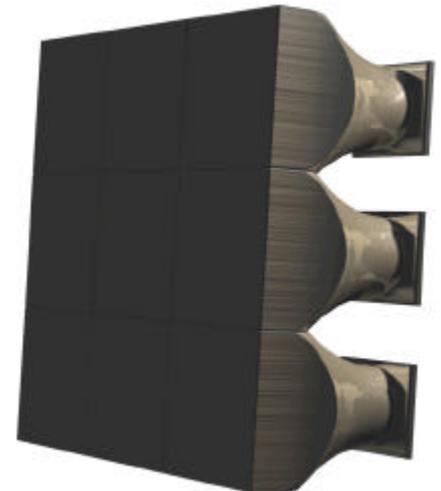
$\sim 10 \text{ mg cm}^{-2} \text{ Gd}_2\text{O}_2\text{S}$



$2 \times 2$  array



$3 \times 3$  array



Single phosphor segment:  
 $105\text{mm} \times 105\text{mm}$

\$600k

\$1.25M

\$1.7M

ADSC Quantum

### CCD X-Ray Detectors

	Quantum 4R	Quantum 210	Quantum 315
<b>Detector Type:</b>	Array (2x2);	Array (2x2);	Array (3x3);
<b>Number of Pixels:</b>	Active area: 188mm x 188mm 2304 x 2304; 5.31 million	Active area: 210mm x 210mm 4096 x 4096; 16.8 million	Active area: 315mm x 315mm 6144 x 6144; 37.75million
<b>Pixel Size at Detector Surfaces:</b>	81.6 x 81.6 microns	51 x 51 microns	51 x 51 microns
<b>Phosphor (optimized):</b>	1 X-ray Angstrom	1 X-ray Angstrom	1 X-ray Angstrom
<b>Spatial Resolution FWHM:</b>	90 microns; 1.1 pixels	90 microns; 1.76 pixels	90 microns; 1.76 pixels
<b>Taper Ratio:</b>	3.7 to 1	3.7 to 1	3.7 to 1
<b>Optical Coupling (CCD to Taper):</b>	Direct bond	Direct bond	Direct bond
<b>CCD Type:</b>	EEV 05-30 AIMO	Thomson THX 7899 (2Kx2K)	Thomson THX 7899
<b>CCD Pixel Size:</b>	22.5 x 22.5 microns	14 x 14 microns	14 x 14 microns
<b>Operating Temperature:</b>	-50 degrees Celcius	-50 degrees Celcius	-50 degrees Celcius
<b>Cooling Type:</b>	Thermoelectric	Thermoelectric	Thermoelectric
<b>Dark Current:</b>	0.03 e/pixel/sec	0.015 e/pixel/sec	0.015 e/pixel/sec
<b>Controller Electronics:</b>	PI ST-138	ADSC Custom	ADSC Custom
<b>Readout Times (Full Resolution):</b>	9 and 3 seconds	1 second	1 second
<b>(2x2-binned):</b>	1 second	330 milliseconds	330 milliseconds
<b>Read Noise (Pixel Rate):</b>	[150 kHz]: 9 electrons typical	[1 MHz]: 18 electrons typical	[1 MHz]: 18 electrons estimated
<b>Full Well Depth (Full Resolution):</b>	440,000 electrons typical	270,000 electrons typical	270,000 electrons typical

??

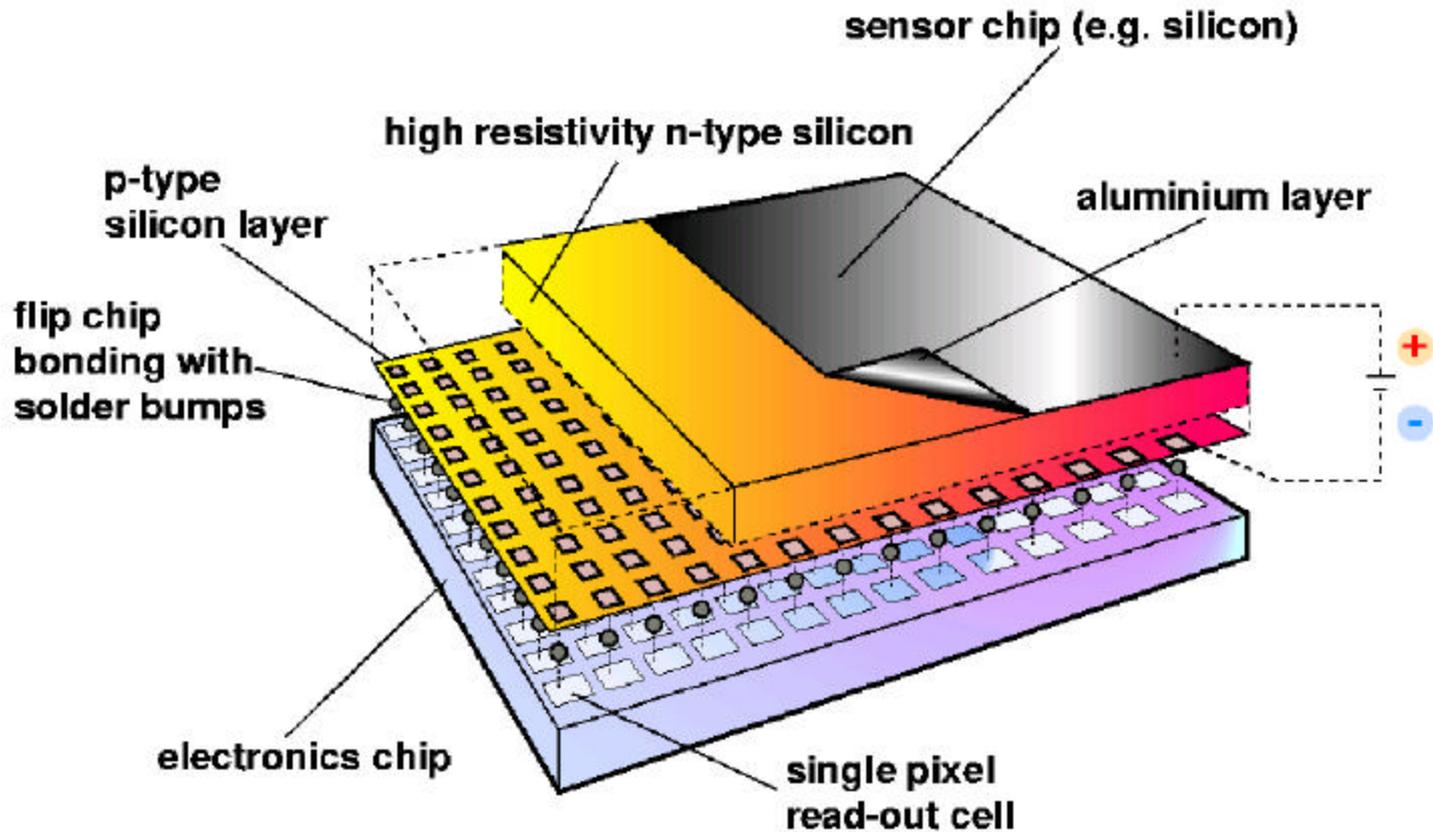
Quantum 420

3x3

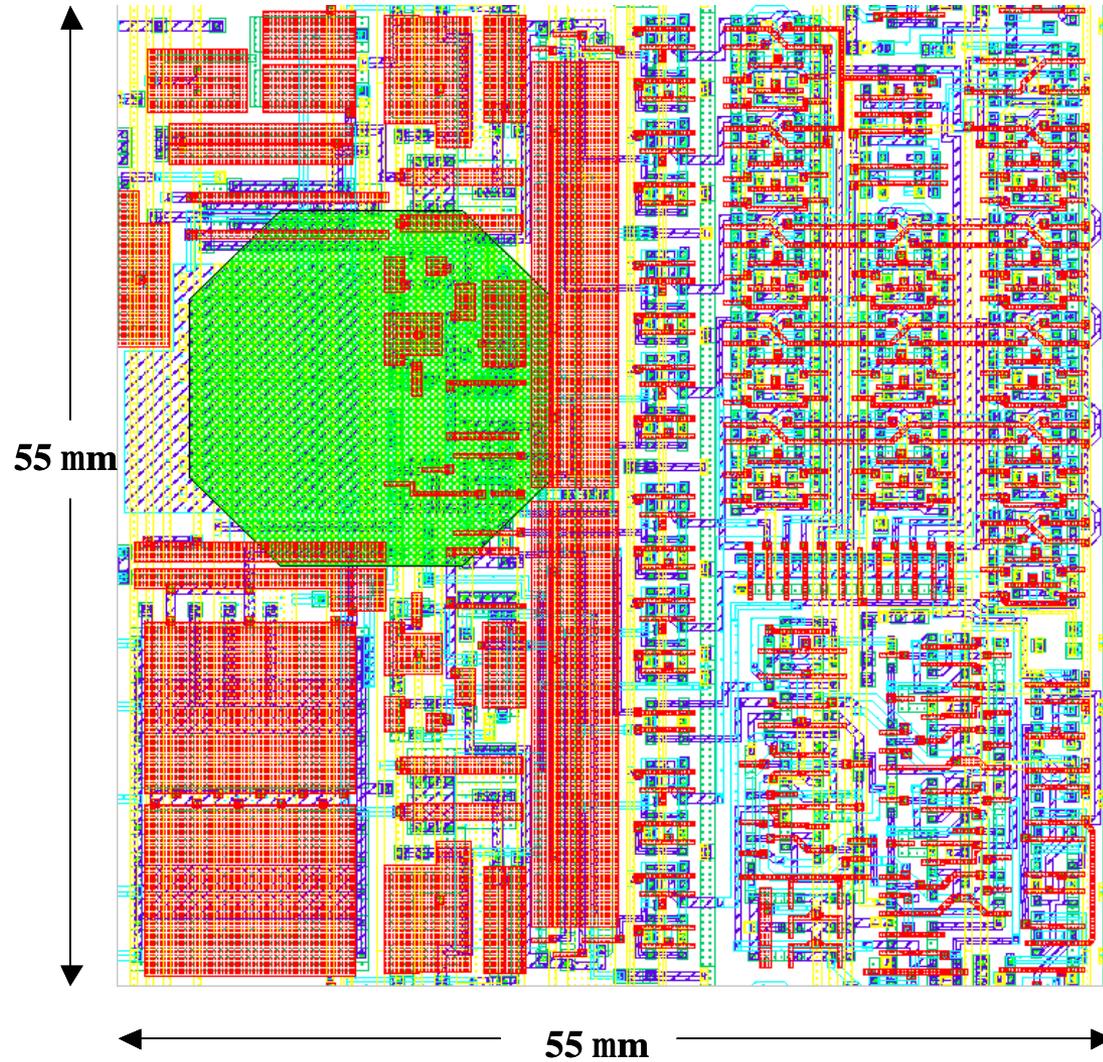
420 mm x 420mm

# Hybrid Pixel Detector

Michael Campbell, CERN



# Medipix2 Cell Layout

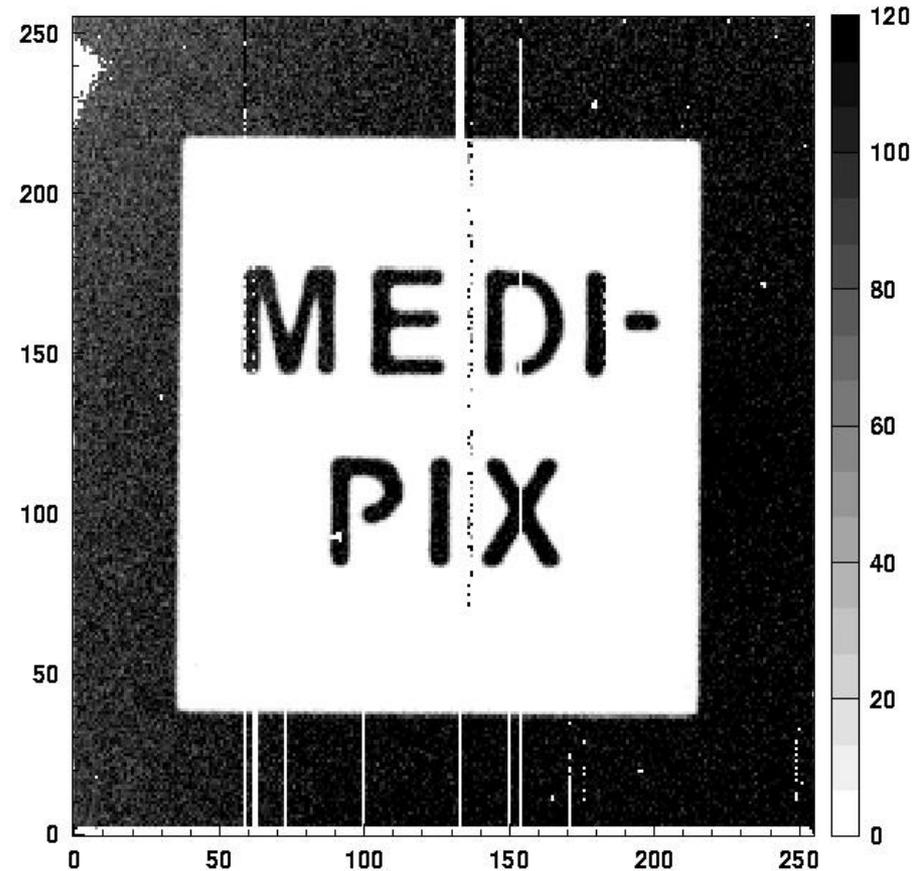
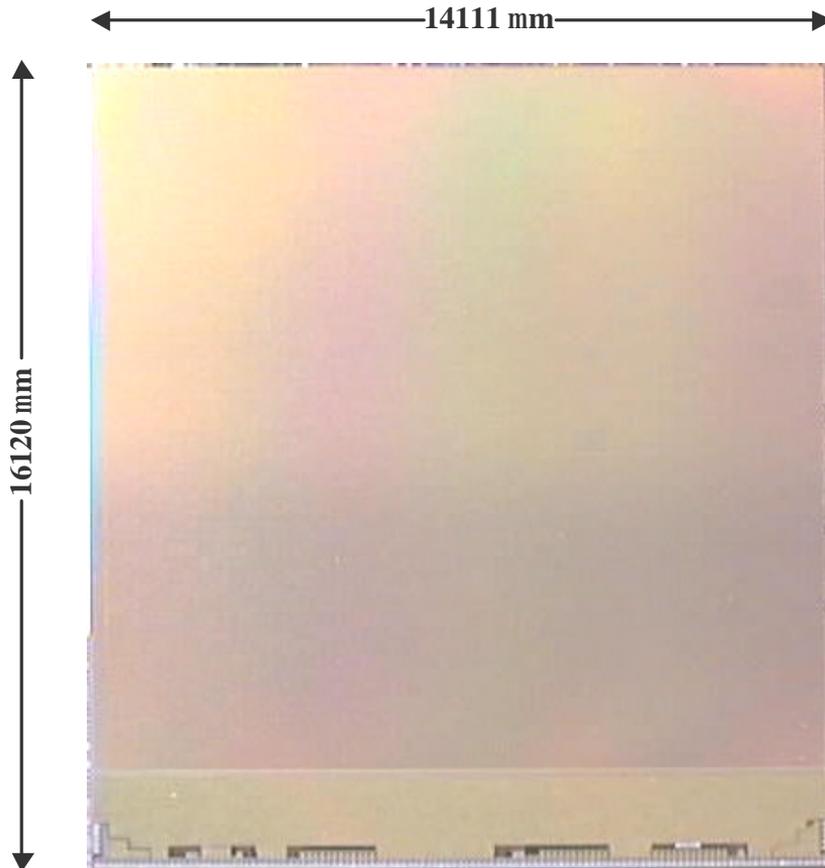


# CERN: Medipix2 Chip Architecture & Performance

Single photon counting, in approximately 70,000 pixels

Limited instantaneous rate, very high dynamic range

$^{109}\text{Cd}$  irradiation

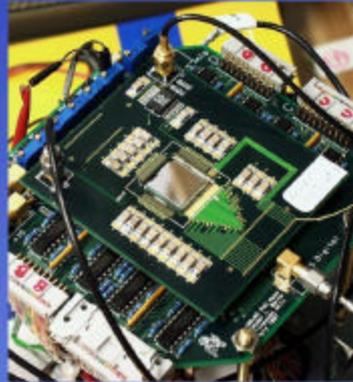


# Charge integration in 9,200 pixels

High instantaneous rate, limited dynamic range

## PAD 100 x 92 pixel Prototype

- 1.2  $\mu\text{m}$  HP CMOS process (MOSIS)  
(Linearized Capacitors)
- 15 x 13.8 mm<sup>2</sup> active area
- 150  $\mu\text{m}$  square pixel
- 300  $\mu\text{m}$  thick, high resistivity Si diode wafer (SINTEF)
- 120  $\mu\text{m}$  solder bump bond  
(GEC-Marconi)



G. Rossi, et al, J Synchrotron Rad., (1999), 6, 1095-1105.

## 100 x 92 Prototype Test results (8.9 keV x-rays)

- Full well capacity (x-rays) 17000
- Non-linearity (% full well) < 0.5 %
- RMS read noise : (x-rays/pixel) 2.0 – 2.8
- Dark current (-20 C) (x-ray/pixel/s) 1.6 – 7.7  
(fA/pixel) 5 – 40
- Storage capacitor leakage 0.07% / s
- PSF (@75 $\mu\text{m}$ ) < 1%
- X-rays stopped in diode 97 %
- Minimum integration period ( $\mu\text{s}$ ) 0.15
- Minimum deadtime between frames ( $\mu\text{s}$ ) 0.6
- Rad damage threshold (kRad in CMOS oxide) 30
- Tolerable radiation dose (kRad) >300

# PADs – Pixel Array detectors

Sol Gruner, CHESS

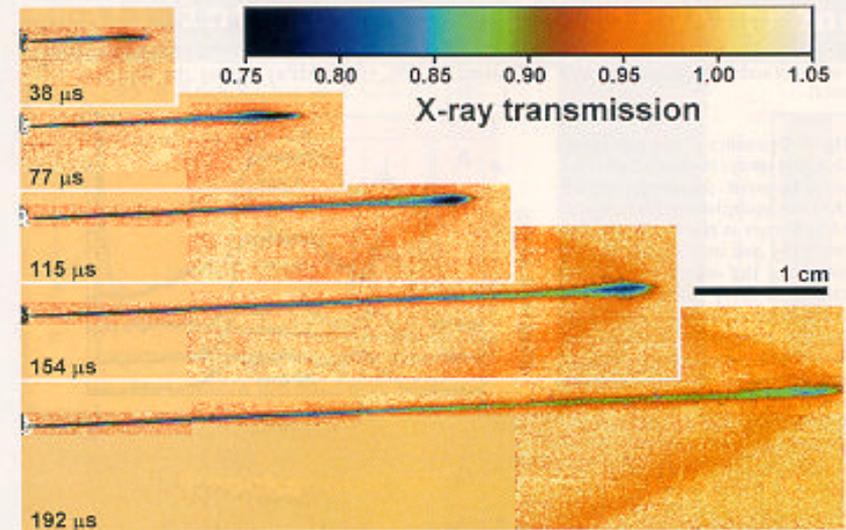
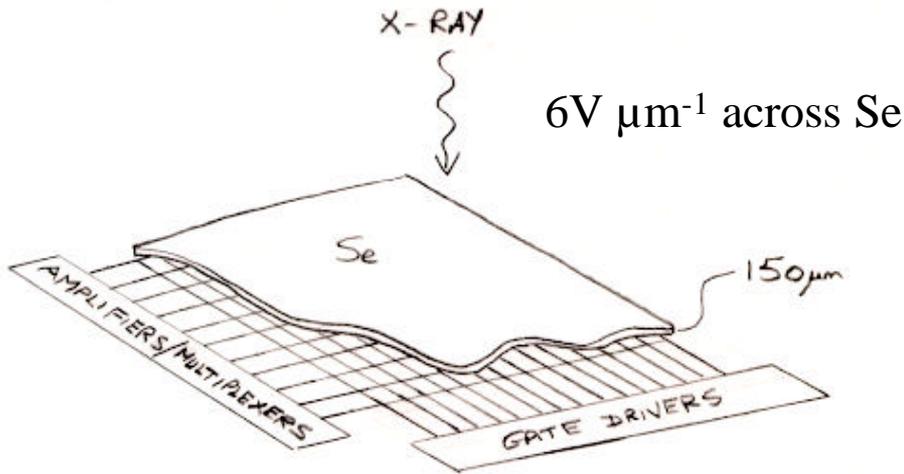


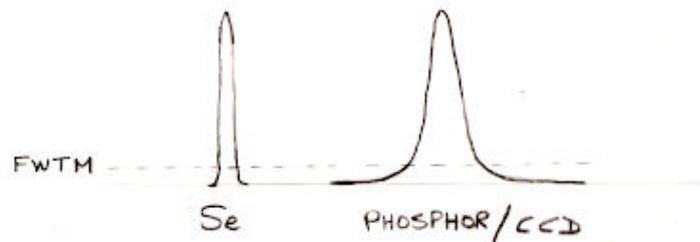
Fig. 3. Time-resolved radiographic images of fuel sprays and the shock waves generated by the sprays for time instances of 38, 77, 115, 154, and 192  $\mu\text{s}$  after the start of the injection (selected from the total of 168 frames taken). The imaged area shown in the largest panel is 61.7 mm (H) by 17.5 mm (V) with data corrected for the divergence of the x-ray beam. Because the x-ray beam size in the experiment was 13.5 mm (H) by 2.5 mm (V), the imaged area was built up by shifting the position of the injector relative to the beam and the PAD and repeating the injection cycle. Boundaries between these areas can be seen upon close inspection. The exposure time per frame was set to 5.13  $\mu\text{s}$  (twice the CHESS synchrotron period) with subsequent images taken after an additional 2.56- $\mu\text{s}$  delay. Each position shown is the average of images from 20 fuel injection cycles. The detector was not positioned over all possible areas of the image, so specific images show missing areas. To optimize the conditions for the direct visualization of the shock waves, we chose the injection pressure to be 135 MPa. The contrast of the shock wave was low, corresponding to only an average of about 15% increase in gas density near the shock front. Therefore, the false-color levels of the images have been set to accentuate small differences in the x-ray intensity arising from the slightly increased x-ray absorption in the compressed  $\text{SF}_6$  gas. The progression of the shock wave can be seen much more clearly in the "movie" of successive frames (26).

Movie at: <http://bigbro.biophys.cornell.edu/>

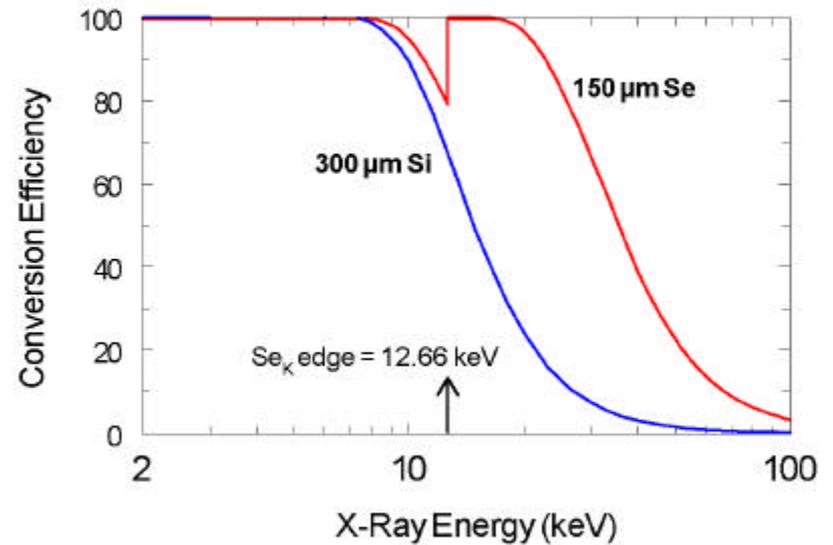
# X-ray Conversion in Selenium



Position response to point beam:



### X-Ray Conversion in Silicon and Selenium



# Selenium Flat Panel Detector

**marresearch**

*420 mm x 350 mm solid state detector*

## Flat Panel Detector

- Fully solid-state technology
- No phosphor involved : The system is based on the direct conversion of X-rays into charges.
- Result: an unprecedented spatial resolution
- No tiling of the active area of 420 mm x 350 mm
- No geometric distortion
- Fast read-out and data storage: one second
- Negligible dark current: No cooling system required

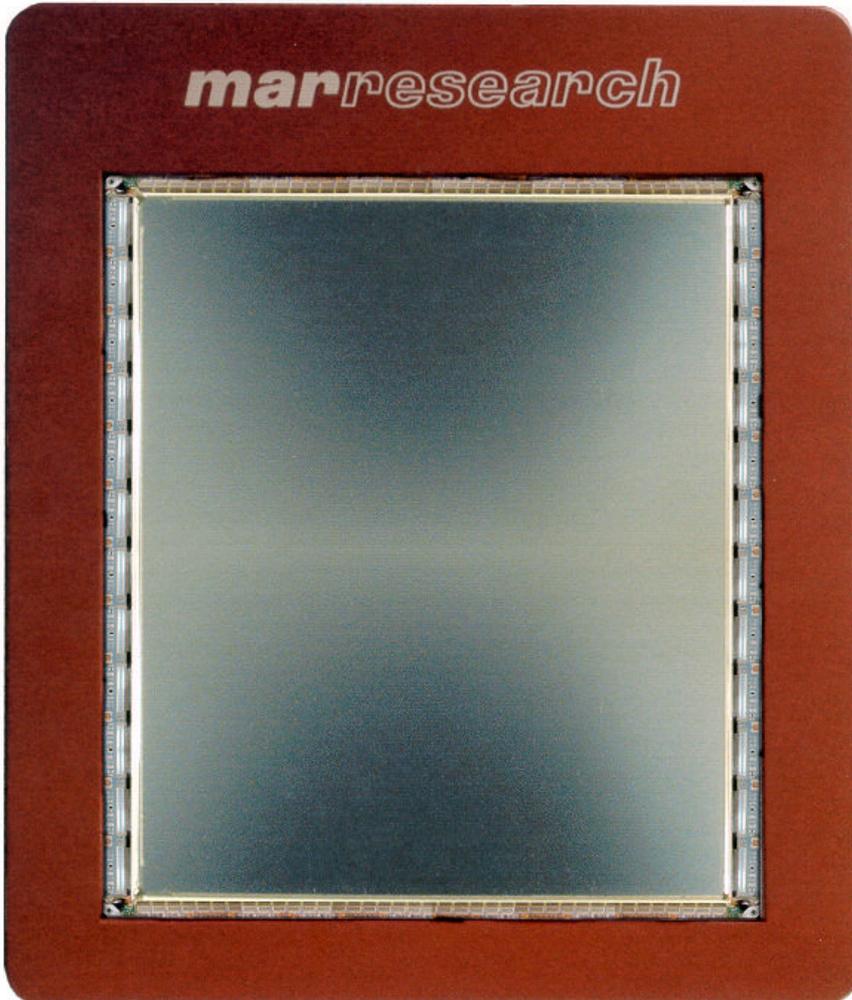
This new fully solid-state detector is based on the direct conversion of the absorbed x-rays into charges. The charges follow electric field lines in the Selenium photoconductor. This direct conversion makes the use of phosphors and optical elements (e.g. optic tapers) obsolete. Consequently, the spatial resolution is extremely high. The point-spread function is well within one pixel. Measurements have shown that the reflection spot sizes and separation depend mainly on the source size, beam size, crystal size and beam divergence. Due to the high spatial resolution, reflections occupy a low number of pixels. The signal-to-noise ratio improves because a lower number of pixels contribute to the background- and read out noise.

### Technical Specifications:

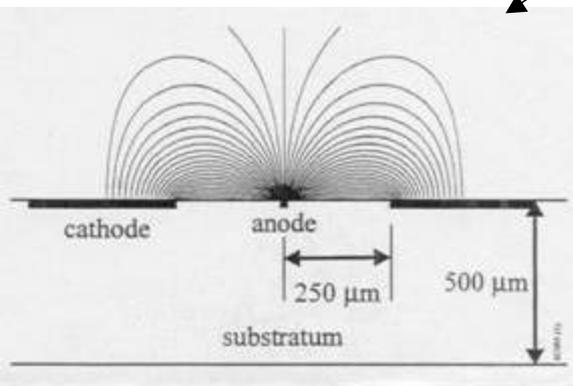
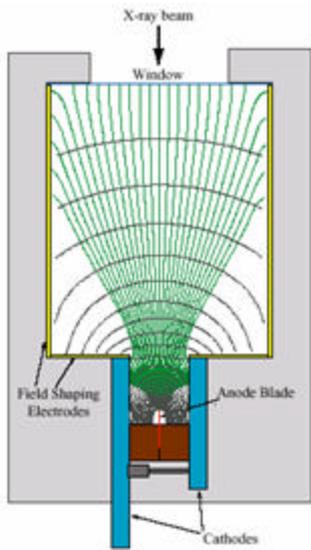
- |                      |   |
|----------------------|---|
| • Size               | Untiled active area of 420 mm x 350 mm            |
| • Pixel size         | 140 $\mu\text{m}$ x 140 $\mu\text{m}$             |
| • Number of pixels   | 7.800.000   |
| • Spatial resolution | point spread function less than 1 pixel           |
| • Dynamic range      | full 16 bit                                       |
| • Sensitivity        | 1 to 1.5 X-rays per ADC-unit, depending on energy |
| • Read noise         | 4 X-rays @ 12 keV                                 |
| • Read-out time      | $\cong$ one second                                |

X-ray Research G.m.b.H.  
Segeberger Chaussee 34  
22850 Norderstedt, Germany

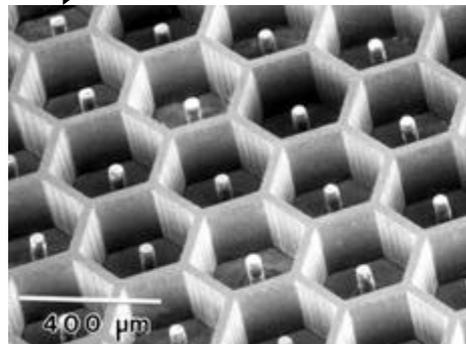
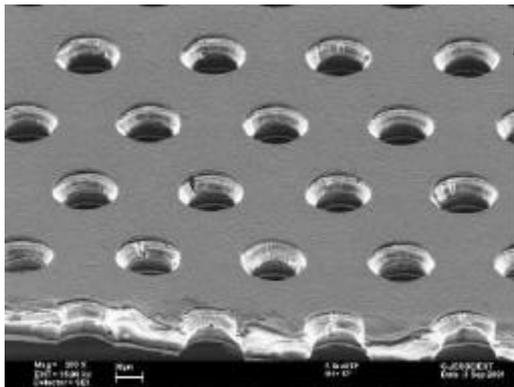
Mar USA, Inc.  
1880, Oak Avenue  
Evanston, IL 60201, USA



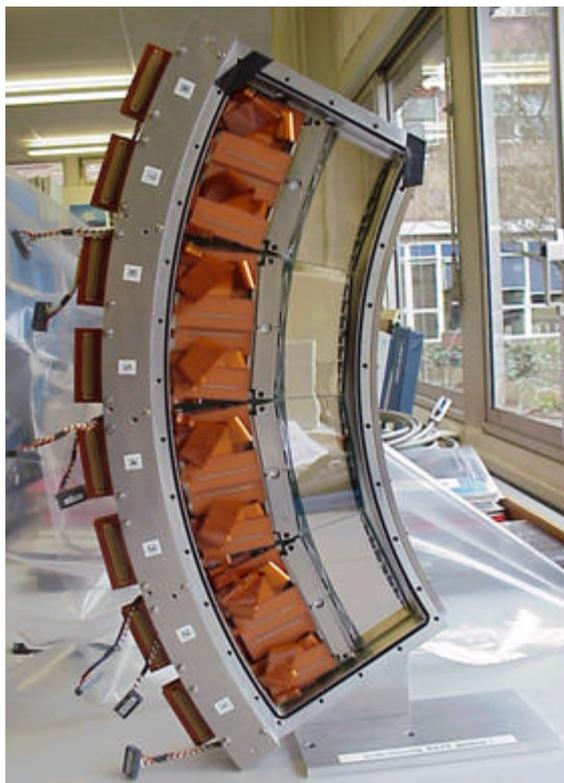
# Micropattern Gaseous Detectors



<i>Acronym</i>	<i>Translation</i>	<i>Origination</i>
Blade	Blade	1980's
MSGC	Micro-Strip Gas Chamber	A. Oed, Grenoble, 1988
MGC	Micro-Gap	R. Bellazzini, Italy, 1995
CAT	Compteur A Trou	F. Bartol et al France 1995
GEM	Gas Electron Multiplier	F. Sauli, CERN 1996
Micromegas	MICRO-Mesh Gaseous Structure	Y. Giomataris, France 1996
MIPA	Micro-Pin Array	P. Rehak, BNL, 1999



# ESFR Beam Line X26



A Fast Position Sensitive Microstrip-Gas-Chamber Detector at High Count Rate Operation

I.P. Dolbnya, H. Alberda, F.G. Hartes, F. Udo, R.E. Bakker, M. Konijnenburg, E. Homan, I. Cerjak,, P. Goettkindt and W. Bras

**Rev. Sci Instrum. 73 (2002) 3754- 3758**

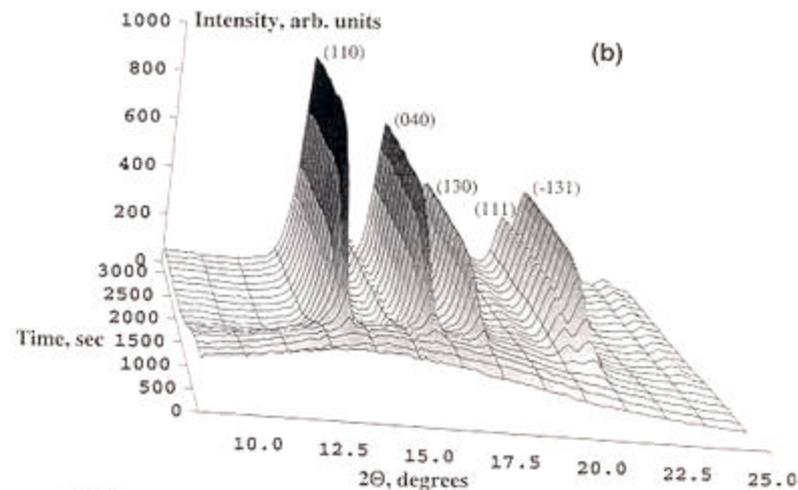


FIG. 6

Time development of WAXS patterns of isothermally crystallizing iPP at 130° demonstrate different stages of the crystallization process (10 keV)

## WAXS MSGC Detector

Count Rate	$4 \times 10^5 / \text{s} / \text{channel}$
Time Resolution	1.5 ms / frame
Energy Range	5-25 keV
Opening Angle	60°
Angular Resn	0.03 °
Radius of curvature	360 mm (from anodes)

# X-ray Absorption Spectroscopy

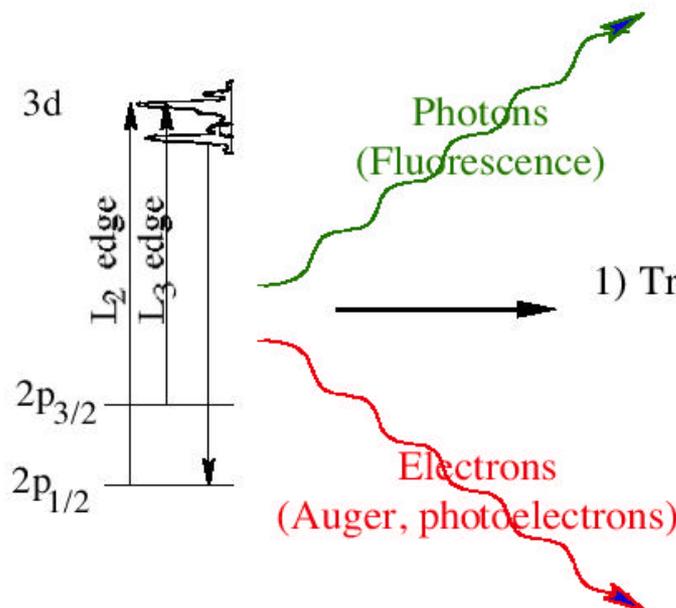
## Synchrotron beam

Intense, monochromatic, tunable  
 $I_0 \approx 10^{12}$  photons/s  
 $\Delta E = 0.1 \text{ eV}$



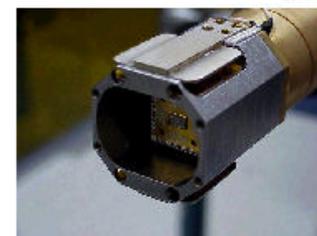
## Sample x

Absorption  $\mu_x(E)$



## Detection

3) Fluorescence  $\propto I_0 \cdot \mu_x(E)$

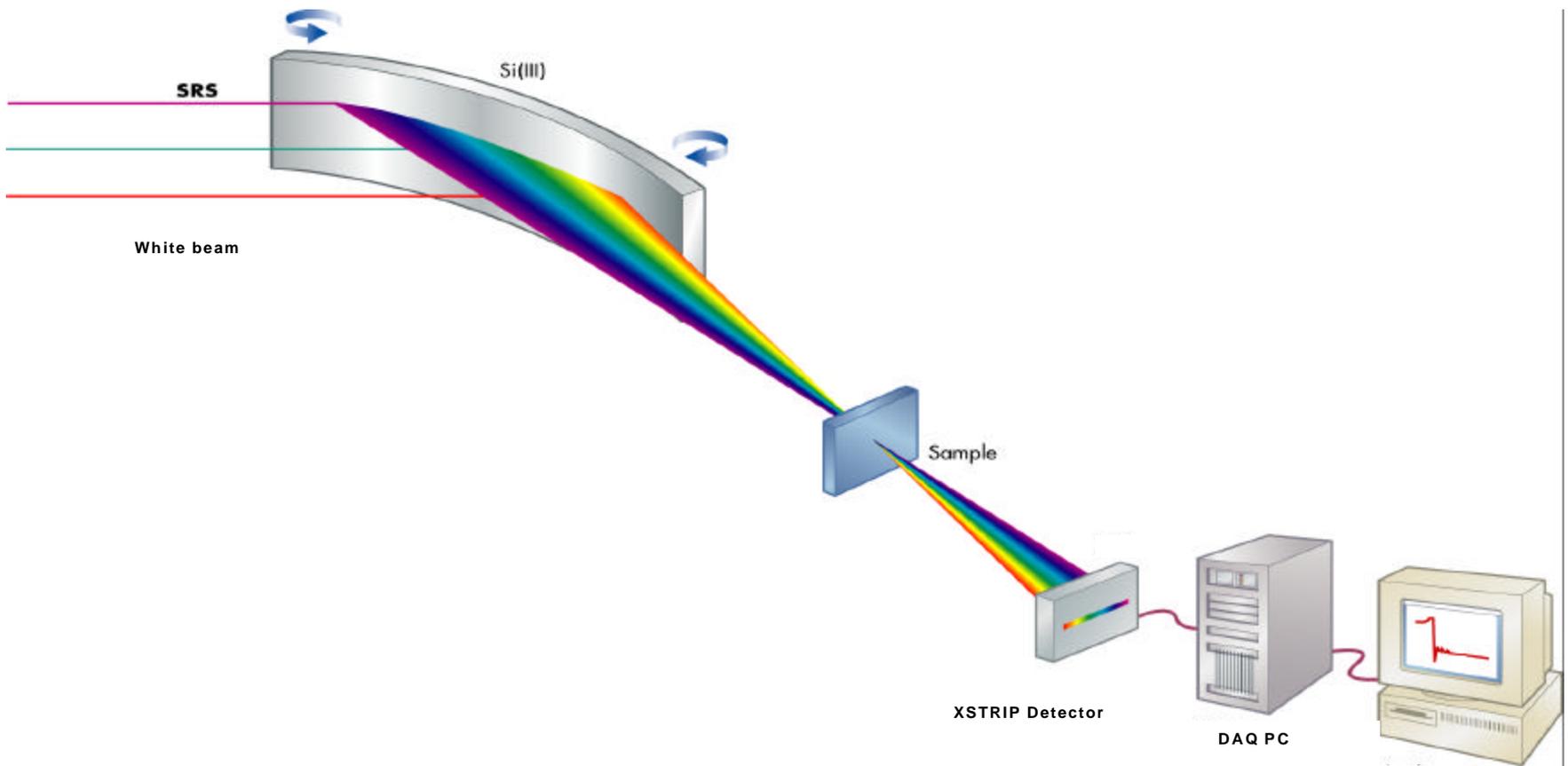


1) Transmission  $\propto I_0 (1 - \mu_x - \mu_{\text{bgnd}})$   
 Thin samples  
 High background

2) Electron signal  $\propto I_0 \cdot \mu_x(E)$   
 Surface sensitive  
 Moderate background

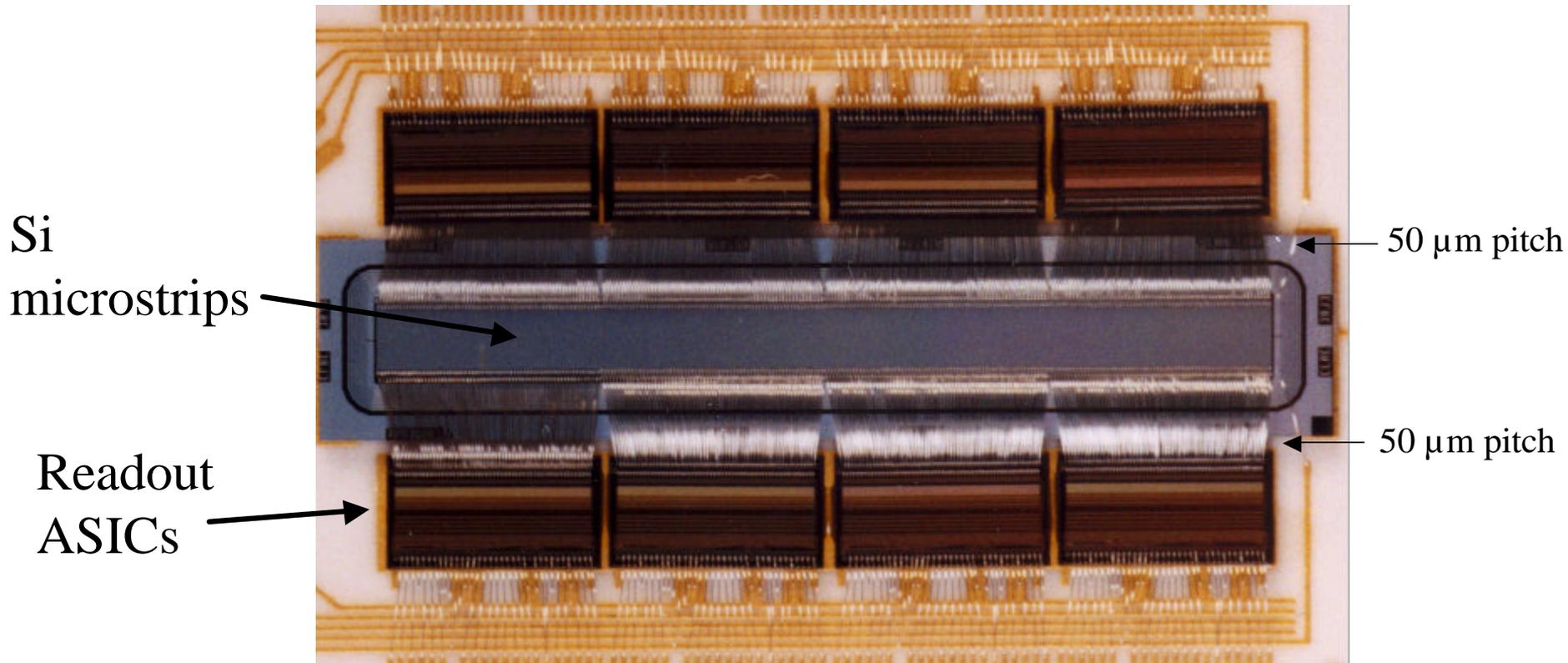
# Energy Dispersive EXAFS (EDE)- Technique

Jon Headspith, Daresbury Laboratory, UK



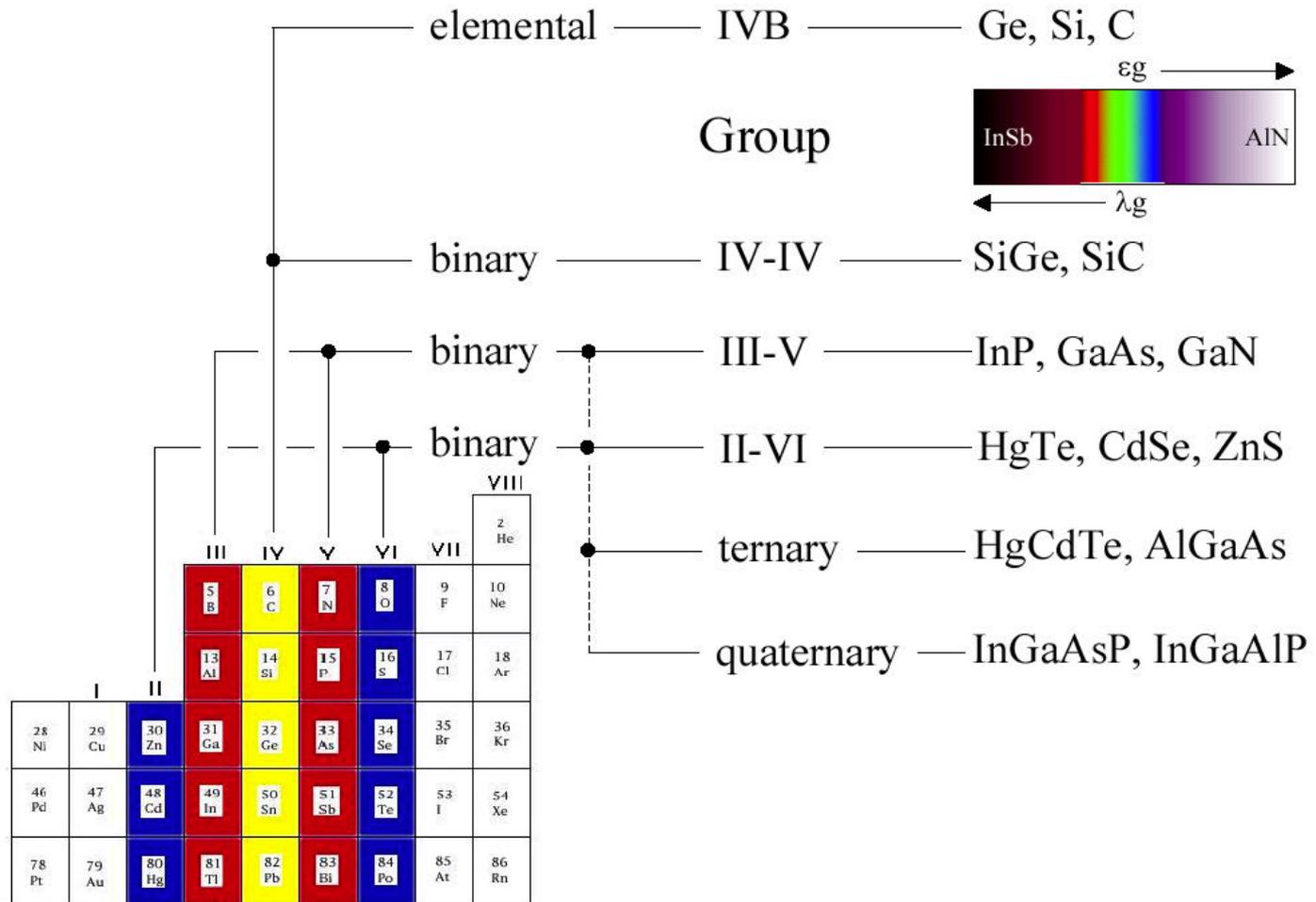
# CCLRC Silicon microstrip based system (XSTRIP)

1024 strips on a 25  $\mu\text{m}$  pitch



# Alan Owens, ESA/ESTEC, The Netherlands

## What are compound semiconductors?



# Advantages of compound semiconductors

- Wide variety of compounds available
- Compounds can be selected for specific environments
- Materials can be engineered for specific applications
- Ability to match response and energy resolution to an application
- **Wide range of stopping powers**  
mass and cost benefits for planetary spacecraft, surgical probes

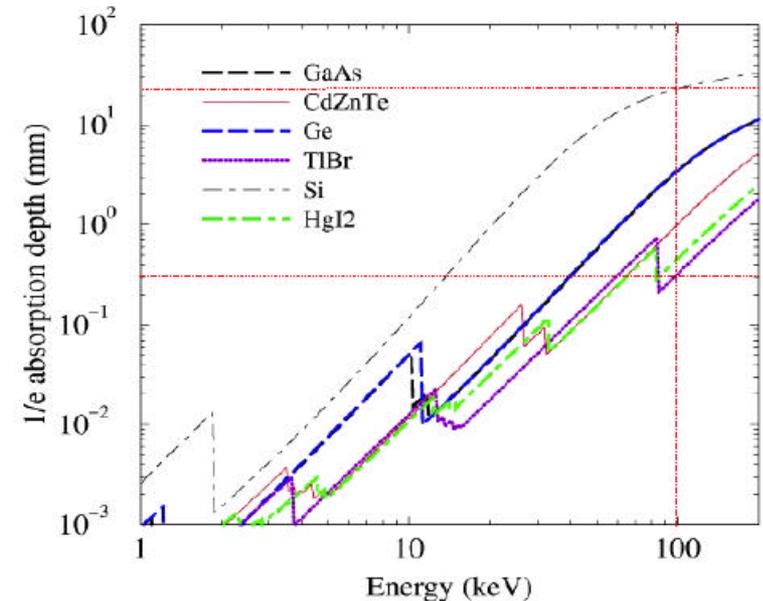
## Material Properties

Summary of some material properties:

	Z	$E_g$ (eV)	$\omega$ (eV/ehp)	$r_i$ at RT ( $\Omega$ )
Diamond	6	5	13	$>10^{13}$
SiC	6/10	3.3	8.4	$10^{13}$
Si	14	1.12	3.6	$\sim 10^4$
Ge	32	0.66	2.0	50
GaAs	31/33	1.4	4.3	$10^8$
InP	49/15	1.4	4.2	$10^7$
CdTe	48/52	1.4	4.4	$10^9$
CdZnTe	48/52	1.6	4.7	$10^{11}$
HgI <sub>2</sub>	80/53	2.1	4.2	$10^{13}$
TlBr	81/35	2.7	5.9	$10^{11}$

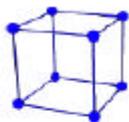
NB, wide range of stopping powers available with similar energy resolutions

40 $\mu$ m of GaAs is equivalent to 500  $\mu$ m Si - same resolution



# Pros and Cons of Current Detector Material

## Si



- ✓ well developed technology
- ✓ heritage
- ✓ well matched to optics
- ✗ limited X-ray response
- ✗ not rad hard
- ✗ cooling issues



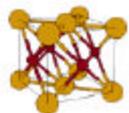
## GaAs



- ✓ near Fano
- ✓ RT operation possible
- ✓ well matched to optics
- ✓ hard X-ray response
- ✓ rad hard
- ✗ development issues



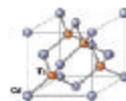
## HgI<sub>2</sub>



- ✓ near Fano
- ✓ RT operation
- ✓ hard X-ray response
- ✓ very rad hard
- ✗ difficult to work with
- ✗ soft



## CdZnTe



- ✓ sub-keV energy resolution
- ✓ hard X-ray response
- ✓ seems rad hard
- ✓ RT operation
- ✗ expensive (HPB)



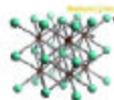
## Ge



- ✓ Fano limited
- ✓ hard X-ray response
- ✗ not rad hard
- ✗ cryogenics
- ✗ fabrication problems



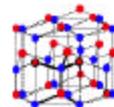
## TlBr



- ✓ sub-keV energy resolution
- ✓ hard X-ray response
- ✓ rad hard
- ✗ polarization effects
- ✗ difficult to work with
- ✗ toxic (genetic modifier)



## SiC

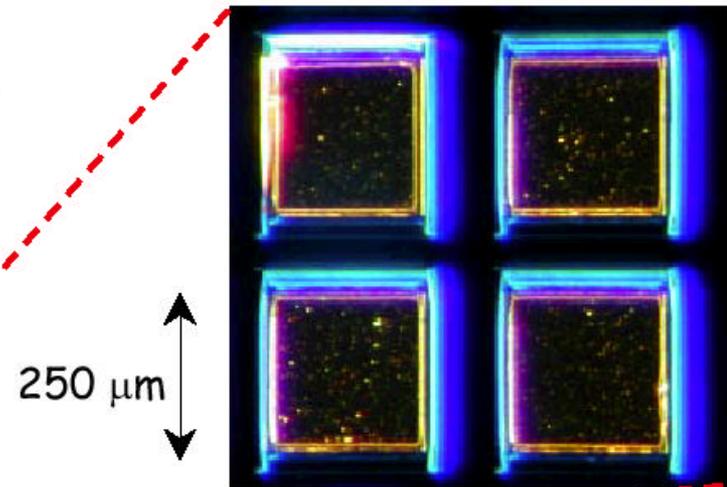
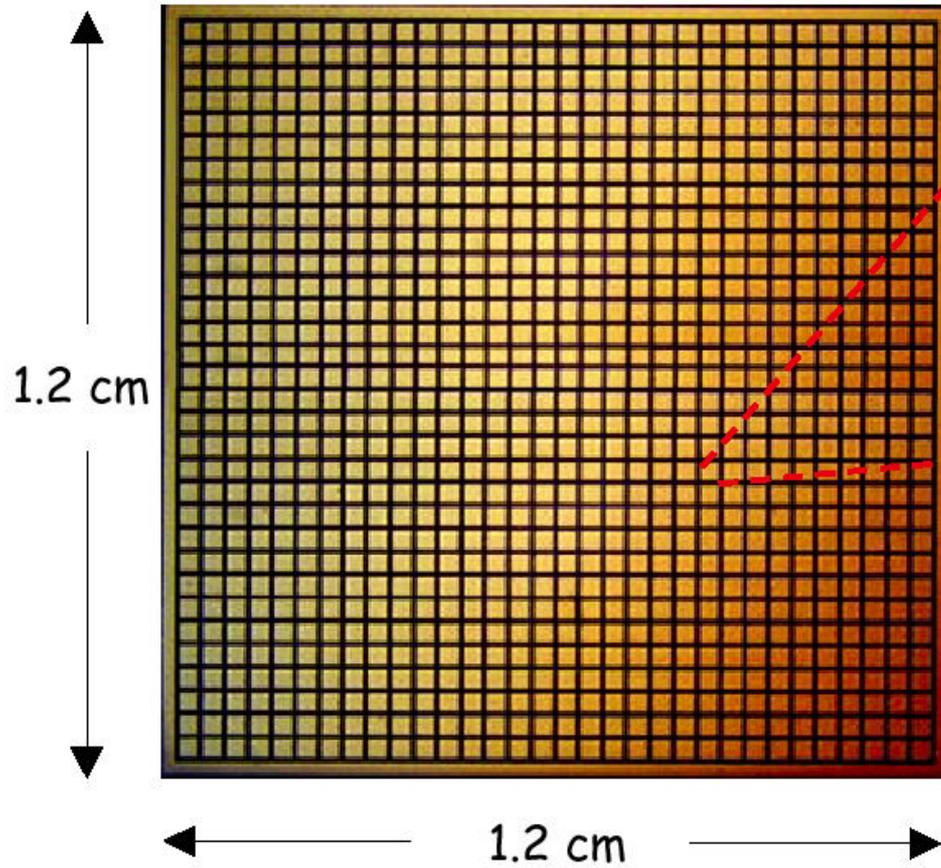


- ✓ keV energy resolution
- ✓ stable, chemically inert
- ✓ very rad hard
- ✗ poor transport properties





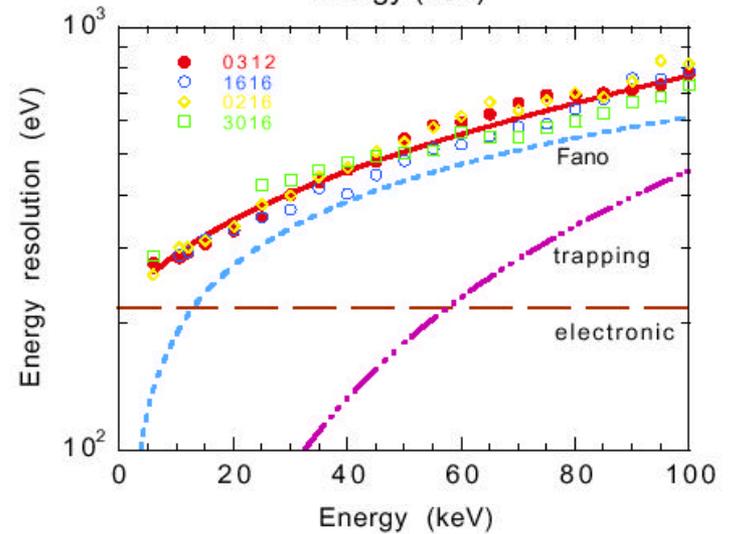
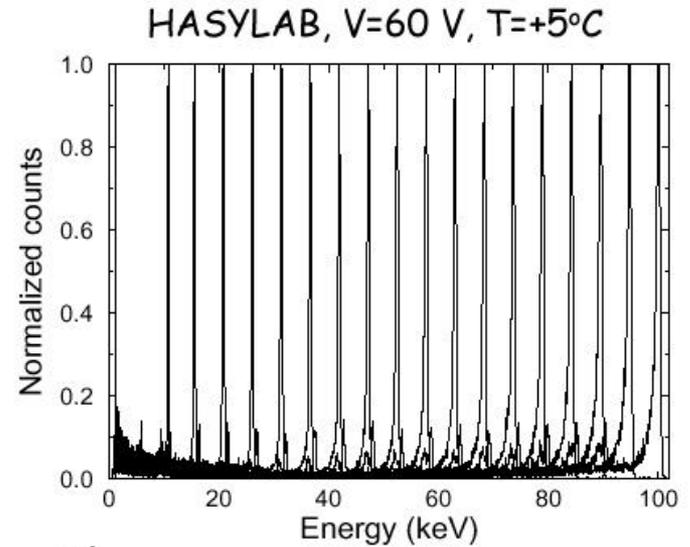
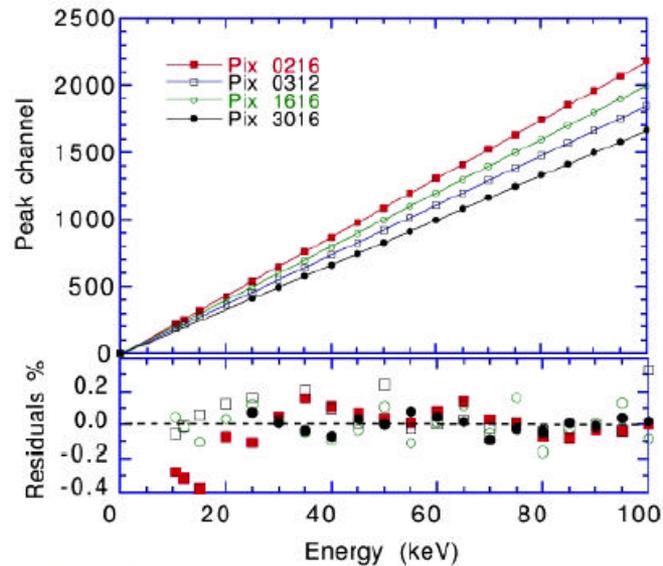
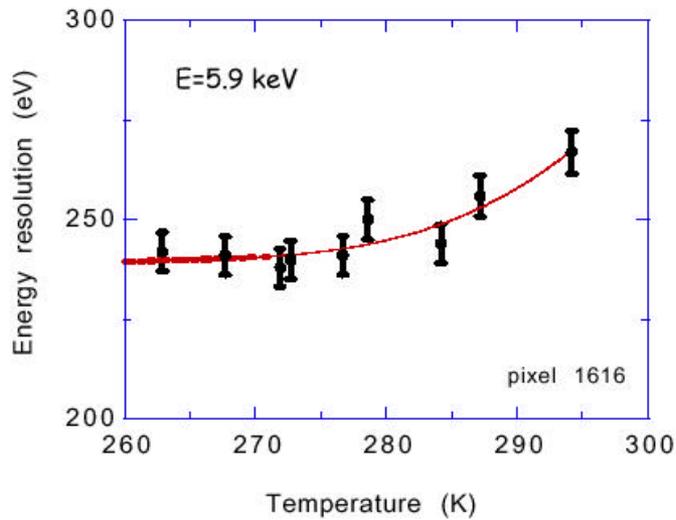
# GaAs 32 x 32 array



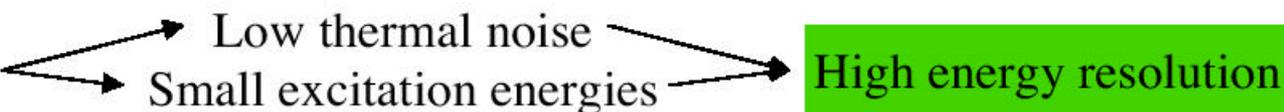
Design goal  $\Delta E=180$  eV @ 5.9 keV

Pitch 300  $\mu\text{m}$ , pixel size 250  $\mu\text{m}$   
Thickness 40  $\mu\text{m}$ , 4  $\mu\text{m}$  p<sup>+</sup>, <1  $\mu\text{m}$  n<sup>+</sup>  
Inter-pixel resistivity > 10<sup>10</sup>  $\Omega$

# GaAs prototype 32 x 32 array - first results



# Outline: Why Cryogenic Detectors?

- Why low T?  Low thermal noise  
Small excitation energies → High energy resolution

- Which technologies?

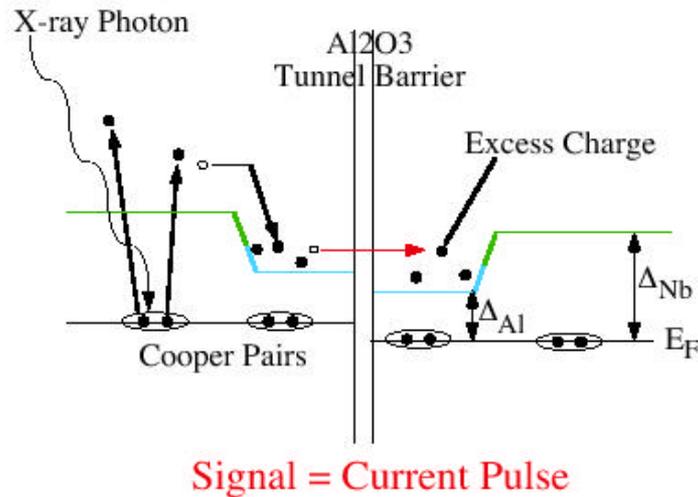
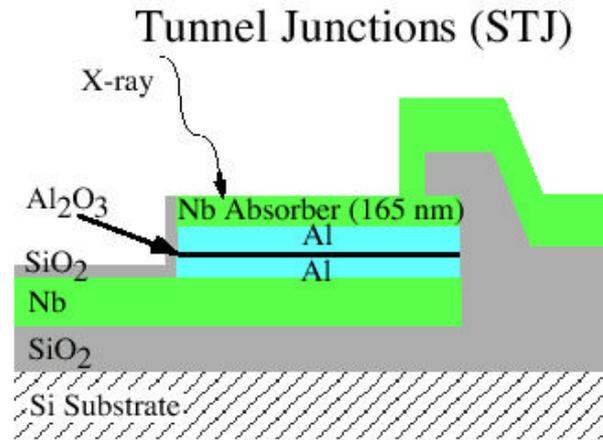
	Tunnel Junctions	Microcalorimeters
Operating Principle	$E \rightarrow \Delta Q$	$E \rightarrow \Delta T$
Resolution (0.1 to 6 keV)	2 - 12 eV FWHM	2 - 5 eV FWHM
Max. count rate	~10,000 cts/s	~500 cts/s

Both detectors have small pixel sizes ( $\sim 0.2 \text{ mm}$ )<sup>2</sup> and are operated around 0.1 K.

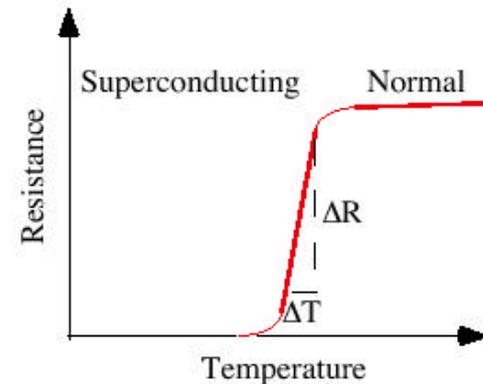
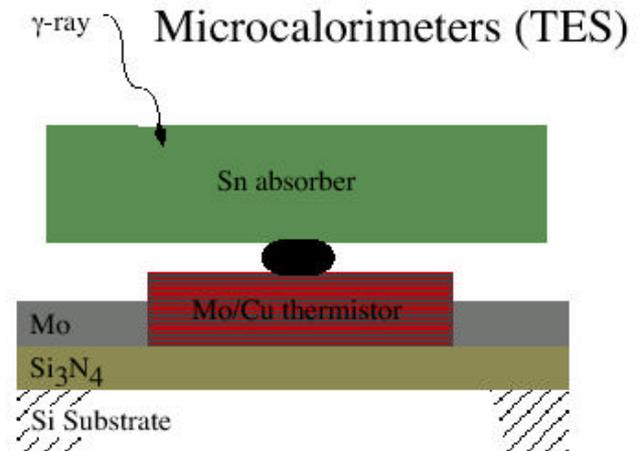
- What for?

Fluorescence-detected absorption spectroscopy of dilute samples

# Superconducting Detector Technologies



High resolution, faster

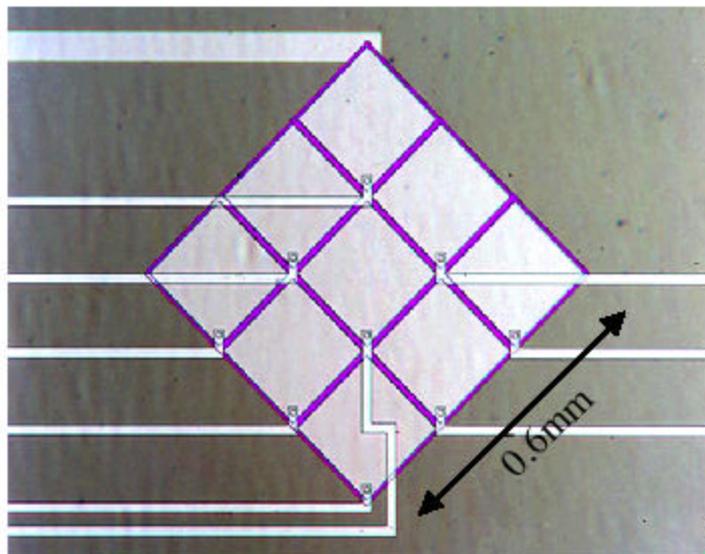


**Signal = Resistance Change**

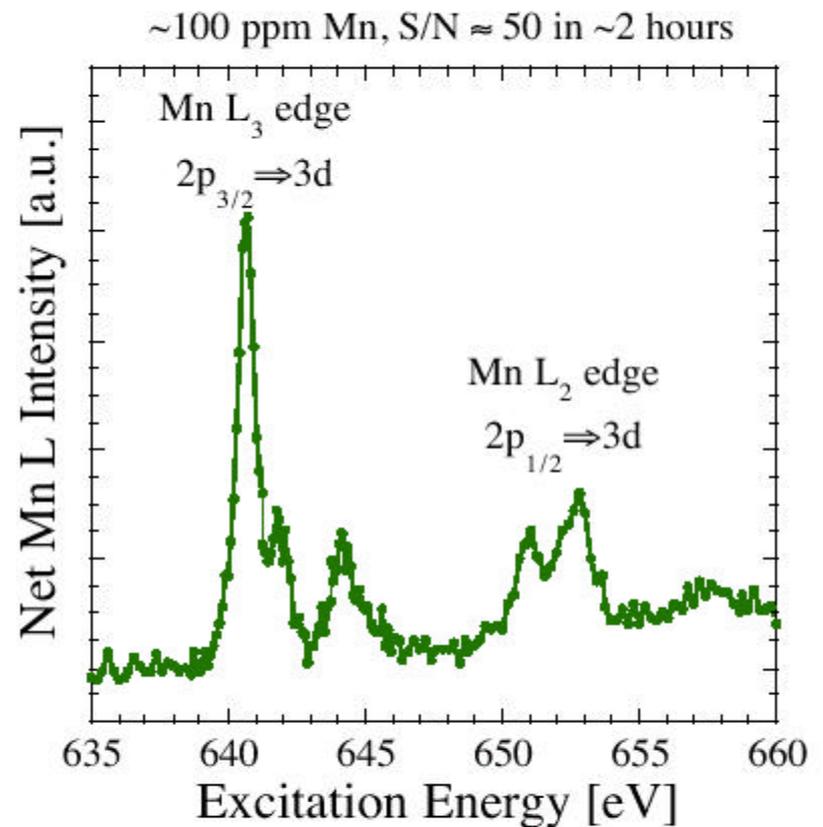
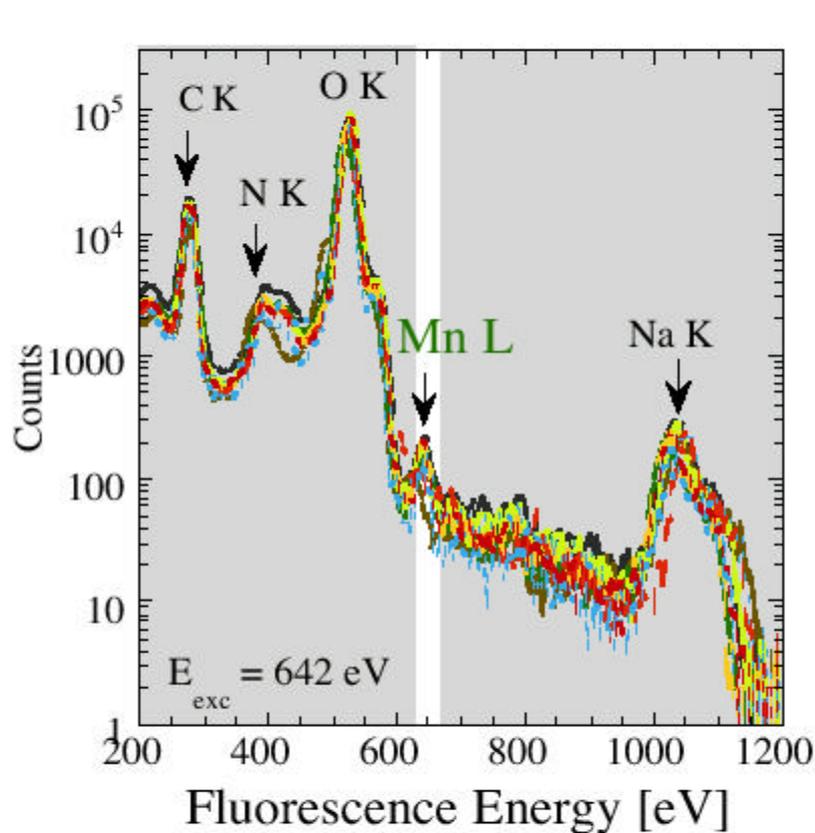
Highest resolution, slower

# Two-Stage ADR with Cold Finger

- 70 mK base T, 20h below 0.4K
- 3×3 array at  $\approx 15\text{mm}$   $\Rightarrow \Omega/4\pi \approx 10^{-4}$
- $\approx 15\text{eV}$  FWHM,  $>100,000$  cts/s max



# X-Ray Absorption Spectroscopy on Proteins



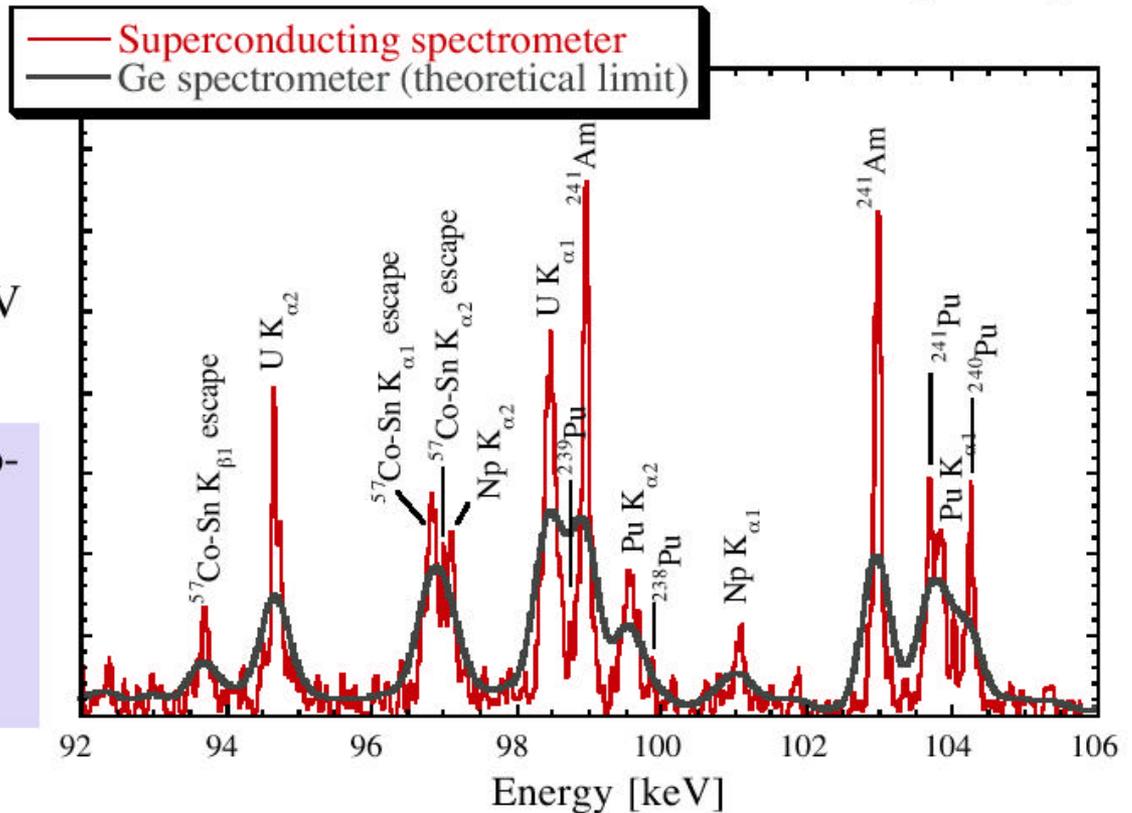
Spectrometer sensitivity is sufficient for  $\sim 100$  ppm samples

# Gamma Ray Spectrometry

First measurements of SNM: Pu mixed isotope sample

$$\Delta E_{\text{FWHM}} \approx 60\text{-}90\text{eV at } 100\text{keV}$$

Superconducting  $\gamma$ -ray spectrometers enable high-resolution spectroscopy in cases where Ge detectors fundamentally limited by device physics.



Some observations:

- Strip/pixel arrays (imaging, spectroscopy...) becoming increasingly popular. ASIC revolution is essential.
- Gas-based detectors continue (and will continue) in niche activities, representing less expensive solutions.
- Significantly more detector R&D support and effort in Europe than in US.